This article was downloaded by:

On: 29 January 2011

Access details: Access Details: Free Access

Publisher *Taylor & Francis*

Informa Ltd Registered in England and Wales Registered Number: 1072954 Registered office: Mortimer House, 37-41 Mortimer Street, London W1T 3JH, UK



Phosphorus, Sulfur, and Silicon and the Related Elements

Publication details, including instructions for authors and subscription information: http://www.informaworld.com/smpp/title~content=t713618290

QUANTUM-CHEMICAL STUDY ON FORMATION OF THIONITROSO COMPOUNDS FROM *N*-CHLORO- SULFENYL-*N*-TRIMETHYLSILYL AMINES

V. V. Penkovsky^a; Yu. G. Shermolovitch^a

^a Institute of Organic Chemistry, Academy of Sciences of Ukraine, Kiev, Ukraine

To cite this Article Penkovsky, V. V. and Shermolovitch, Yu. G.(1993) 'QUANTUM-CHEMICAL STUDY ON FORMATION OF THIONITROSO COMPOUNDS FROM N-CHLORO- SULFENYL-N-TRIMETHYLSILYL AMINES', Phosphorus, Sulfur, and Silicon and the Related Elements, 80: 1, 255 - 258

To link to this Article: DOI: 10.1080/10426509308036898 URL: http://dx.doi.org/10.1080/10426509308036898

PLEASE SCROLL DOWN FOR ARTICLE

Full terms and conditions of use: http://www.informaworld.com/terms-and-conditions-of-access.pdf

This article may be used for research, teaching and private study purposes. Any substantial or systematic reproduction, re-distribution, re-selling, loan or sub-licensing, systematic supply or distribution in any form to anyone is expressly forbidden.

The publisher does not give any warranty express or implied or make any representation that the contents will be complete or accurate or up to date. The accuracy of any instructions, formulae and drug doses should be independently verified with primary sources. The publisher shall not be liable for any loss, actions, claims, proceedings, demand or costs or damages whatsoever or howsoever caused arising directly or indirectly in connection with or arising out of the use of this material.

Communication

QUANTUM-CHEMICAL STUDY ON FORMATION OF THIONITROSO COMPOUNDS FROM N-CHLORO-SULFENYL-N-TRIMETHYLSILYL AMINES

V. V. PENKOVSKY† and Yu. G. SHERMOLOVITCH

Institute of Organic Chemistry, Academy of Sciences of Ukraine, Murmanskaya 5, Kiev 253094, Ukraine

(Received December 15, 1992; in final form March 8, 1993)

The MNDO quantum-chemical calculations revealed that the N-chlorosulfenyl-N-trimethylsilyl amine decomposition scheme may be described as the S—Cl bond weakening and the subsequent trimethylsilyl group transfer to the chlorine atom, with the activation barrier of 260–294 kJ/mol.

Key words: N-chlorosulfenyl-N-trimethylsilyl amines; thionitroso compounds; MNDO calculations; reaction mechanisms.

INTRODUCTION

Thermolysis of N-chlorosulfenyl-N-trimethylsilyl alkyl amines and 1,1-dihydro-polyfluoroalkyl amines (1) leads to the formation of unstable thionitroso compounds (2) proved by isolation of their (4 + 2)-cycloaddition products:^{1,2}

RN(SiMe₃)SCl
$$\xrightarrow{\Delta}$$
 RN=S $\xrightarrow{}$ adduct 1 $\xrightarrow{}$ -Me₃SiCl 2 $R = i$ -Pr, t -Bu, CH₂(CF₂)₂H, CH₂(CF₂)₆H

Mechanism of the trimethylsilyl chloride elimination from the compounds 1 is unknown.

RESULTS AND DISCUSSION

We performed the quantum-chemical investigation of the geometrical and electronic structure of molecules RN(SiH₃)SCl (3a, R = Me, 3b, R = t-Bu, 3c, R = CH₂CF₃) being models of the compounds 1. The MNDO method was used with complete geometry optimization. The structure of molecule <math>3a is shown in Figure 1(a); differences in geometrical parameters of molecules 3b, c are insignificant. The nitrogen hybridization is of the sp²-type in molecules 3a, b and close to the sp²-type

[†]Author to whom correspondence should be addressed.

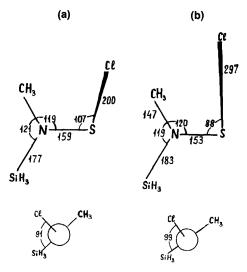


FIGURE 1 Geometrical parameters and Newman projections along the S—N bond for molecule 3a in the ground state (a) and transition state (b); bond lengths in picometers, valence bond angles in degrees.

in molecule 3c. The S—N and C—N bonds are simple covalent ones as is evidenced by their lengths and Wiberg indices (Table I). The Si—N bond is strongly polarized as follows from the high positive charge on the silicon atom and the negative charge on the nitrogen atom (another negatively charged centre in molecules 3a-c is the chlorine atom). The S—Cl bond is practically orthogonal to the CNS plane, its index being very low. Thus, geometrical and electronic structure of molecules 3a-c suggests the intramolecular rearrangement with the S—Cl bond cleavage.

We studied a theoretical model of this reaction for molecules $3\mathbf{a}-\mathbf{c}$. The reaction coordinate was the S—Cl bond length (d_{SCl}) varied in the range of 200–400 pm. For all systems, enthalpy curve has a maximum at $d_{SCl}=292-297$ pm with the simultaneous Si—N bond lengthening, S—N bond shortening and CNS valence bond angle decrease in comparison with the ground state (Figure 2). A comparative analysis of energy values in the vicinity of the obtained enthalpy profile leads to the conclusion that the enthalpy maximum corresponds to the transition states (TS) of molecules $3\mathbf{a}-\mathbf{c}$. The geometrical parameters of molecule $3\mathbf{a}$ are presented in Figure 1(b). In TS the maximal negative charge is localized on the chlorine atom;

TABLE I
Charges on atoms and bond indices of molecules 3a-c

Mole- cule	Charge on atom, e					Bond index			
	S	N	Si	Cl	Ca	SN	SCI	SiN	CN
3a	+0.29	-0.74	+1.66	-0.27	+0.19	1.06	0.84	0.65	0.95
3a ^b	+0.37	-0.54	+1.67	-0.67	+0.13	1.93	0.37	0.55	0.94
3b	+0.28	-0.72	+1.66	-0.27	+0.05	1.07	0.83	0.65	0.93
3c	+0.28	-0.74	+1.67	-0.22	+0.16	1.04	0.89	0.62	0.99

^aAtom C of the C-N bond.

bTS.

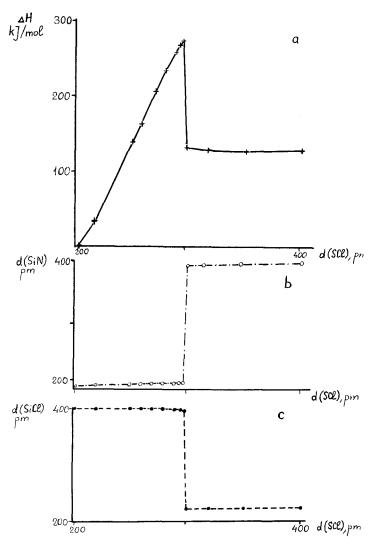


FIGURE 2 Reaction enthalpy profile (a) and changes of interatomic distances d_{SiN} (b) and d_{SiCI} (c) versus the reaction coordinate d_{SCI} for the decomposition of compound 3a.

both the S—Cl and the Si—N bonds are considerably weakened while the S—N bond is strengthened in comparison with the ground state (see Table I). So migration of the electron-deficient SiH₃ group to the chlorine atom is favoured to form SiH₃Cl and a compound 2. In fact, further growth of the $d_{\rm SCl}$ value causes a drastic increase of the Si—N distance up to 400-420 pm and a decrease of the $d_{\rm SiCl}$ value to 212 pm (Figure 2) giving evidence for the cleavage of the Si—N bond and the formation of the Si—Cl bond. The S—N bond length is simultaneously decreased to the value of 149 pm typical for the compounds 2 in the MNDO calculations.²

Consequently, the decomposition of compounds 3a-c may be schematically described as the S—Cl bond weakening and the subsequent silyl group transfer to

the chlorine atom. The activation barrier of this process for compounds $\bf 3a$, $\bf 3b$ and $\bf 3c$ is estimated to be 274, 260 and 294 kJ/mol, respectively, thus increasing for electron-withdrawing substituents. It should be borne in mind, however, that in our investigation only the potential curve of the considered reaction was calculated, while in a complete theoretical study the potential energy surface should be constructed. The latter one is a function of M = 3N - 6 independent internal coordinates (nuclear degrees of freedom) where N is the number of nuclei, and a real microscopic reaction pathway includes vibrational and rotational motions within this multidimensional hyperspace. The M value is 27 for the compound $\bf 3a$ and 54 for $\bf 3b$; surely, the required body of calculations would be rather large. Therefore our simplified approach may be acceptable as an overall thermodynamic description for the decomposition process of compounds $\bf 3a-c$.

Changes in geometrical and electronic structure of organoelement compounds after substitution of the SiH₃ group by the SiMe₃ group are negligible.³ Thus, our conclusion about the mechanism of the considered reaction may be extended on the compounds 1, too.

REFERENCES

- L. N. Markovsky, A. V. Solovyov, E. I. Kaminskaya, A. V. Borodin and Yu. G. Shermolovitch, Zh. Org. Chim., 26, 2083 (1990).
- L. N. Markovsky, A. V. Solovyov, V. V. Penkovsky, N. P. Kolesnik, A. V. Borodin, S. V. Iksanova and Yu. G. Shermolovitch, Zh. Org. Chim., 28, 1388 (1992).
- 3. V. V. Penkovsky, V. I. Kharchenko and L. N. Alexeiko, Teoret. i Eksper. Chim., 27, 462 (1991).